



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Gary M. Moore
Assignee: Moore Epitaxial Inc.
Title: METHOD OF CONTROLLING GAS FLOW TO A SEMICONDUCTOR PROCESSING REACTOR
Serial No.: 09/765,919 Filed: January 18, 2001
Examiner: Chen, Bret P. Group Art Unit: 1762
Docket No.: MTEC101001

Monterey, CA
November 6, 2002

CLEAN COPY OF DESCRIPTION REPLACEMENT PARAGRAPH(S)

Replace the paragraph extending from Page 4, line 29 to Page 5, line 5 with:

--After the high dopant concentration process gas was fully removed from reactor 14, the lightly doped P type silicon layer was deposited. Valve 42 was opened and process gas A, hereinafter referred to as low dopant concentration process gas, flowed through MFC 32 through valve 42 to exhaust 23 until the mass flow rate of the flow through MFC 32 stabilized. Valve 40 was opened and valve 42 was closed thereby providing the low dopant concentration process gas into reactor 14. The low dopant concentration process gas reacted with heated substrates 16 and formed the lightly doped P type silicon layer on substrates 16.--

Replace the paragraph extending from Page 9, line 11 to line 24 with:

--Also in accordance with the present invention, a method of controlling gas flow to a reactor includes opening a first gas manifold inlet valve coupled between a first mass flow controller, e.g., a first regulator, and a gas manifold and regulating a mass flow rate of a flow of a first process gas through the first gas manifold inlet valve to the gas manifold with the first mass flow controller. The method further

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includes opening a gas manifold exhaust valve coupled between a second mass flow controller, e.g., a second regulator, and an exhaust and regulating a mass flow rate of a flow of a second process gas through the gas manifold exhaust valve to the exhaust with the second mass flow controller.--

Replace the paragraph extending from Page 13, line 16 to line 23 with:

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--For example, a process gas may be supplied to point of use 501 by gas flow controller system 500 to grow a layer on a semiconductor substrate. Short process gas supply line 506 significantly reduces or even eliminates the prior art problem of creating a transition layer after gas flow controller system 500 disconnects the process gas line or lines in the plurality of process gas lines 505 providing the process gas.--

Replace the paragraph extending from Page 14, line 2 to line 18 with:

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--Thus, gas flow controller system 500 of this invention permits formation of abrupt transitions between layers on a substrate using prior art processing equipment without modification to the processing reactor itself or installation of new substrate processing equipment. However, in one embodiment, to enhance formation of abrupt transitions between layers on a substrate, gas flow controller system 500 of this invention is used in combination with a gas dispersion head of Moore et al., related and commonly assigned U.S. Patent Application Serial No. 09/399,115, now U.S. Patent No. 6,475,284, issued November 5, 2002, entitled "GAS DISPERSION HEAD", which is herein incorporated by reference in its entirety. Since this invention eliminates the need to obtain new processing reactors, the cost of production of substrates with state of the art feature sizes is reduced.--

Replace the paragraph extending from Page 17, line 24 to Page 18, line 5 with:

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November 6, 2002
Date of Signature

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